

# Intel, Micron Sampling Industry-Leading Multi-Level Cell NAND Flash Memory

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Intel Corporation and Micron Technology, Inc., today announced they are sampling industry-leading 50 nanometer multi-level cell (MLC) NAND flash memory manufactured by their NAND flash memory joint venture, IM Flash Technologies.

The new MLC NAND flash memory components feature a world-class die and cell size ideally suited for use in today's computing and consumer electronics devices that are increasingly smaller and more efficient themselves. The 50nm MLC technology, sampling at a 16 gigabit (Gb) die density, complements the previously announced 50nm single-level cell (SLC) products that the companies are shipping today at a 4 Gb die density.

The new MLC NAND product caps a year of productive activity in which Intel and Micron have aggressively ramped a state-of-the-art 300 millimeter (mm) flash manufacturing factory network and are in the midst of developing sub-40nm NAND flash memory products.

"In only one year, Micron and Intel have developed the industry's leading NAND flash memory MLC product and aggressively ramped a factory network that is delivering today for our customers," said Micron Chief Operating Officer Mark Durcan. "We're proud of the accomplishments we're achieving with Intel, and we look forward to more milestones in the next year."

"The progress of our joint venture with Micron to develop industry-

leading architecture has surpassed our expectations during this first year,” said Randy Wilhelm, Intel vice president and general manager, NAND Products Group. "Intel and Micron were the first in the industry to introduce 50nm SLC NAND samples last July, and developing the industry's most advanced 50nm MLC architecture is a further proof point to the strength of this development and manufacturing relationship."

Along with producing NAND flash out of Micron facilities in Boise, Idaho, and Manassas, Va., the IM Flash joint venture has also been manufacturing wafers since February at a 300mm facility in Lehi, Utah, that is completely dedicated to the joint venture. Additionally, the companies are moving forward on plans to bring a new IM Flash manufacturing facility to Singapore with their recently announced Singapore partnership.

Source: Intel

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